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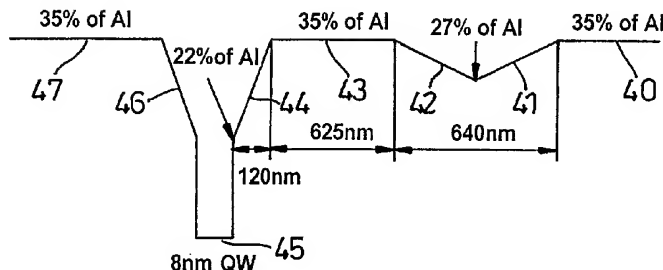
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(54) Title: CONTROL OF OUTPUT BEAM DIVERGENCE IN A SEMICONDUCTOR WAVEGUIDE DEVICE



(57) Abstract: A semiconductor laser device incorporates a beam control layer (42, 41) for reducing far field and beam divergence. Within the beam control layer, a physical property of the semiconductor material varies as a function of depth through, the beam control layer, by provision of a first sub-layer (42) in which the property varies gradually from a first level to a second level, and a second sub-layer (41) in which the property varies from said second level to a third level. In the preferred arrangement, the conduction band edge of the semiconductor has a V-shaped profile through the beam control layer.

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